

## Silicon NPN Power Transistors

2SC4370

## DESCRIPTION

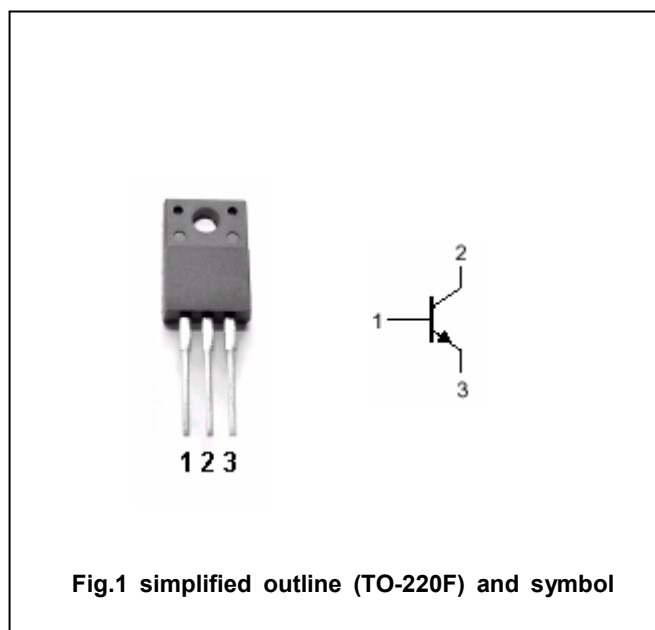
- With TO-220F package
- Complement to type 2SA1659
- High transition frequency

## APPLICATIONS

- High voltage applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	160	V
$V_{CEO}$	Collector-emitter voltage	Open base	160	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		1.5	A
$I_B$	Base current		0.15	A
$P_C$	Collector dissipation	$T_C=25^\circ\text{C}$	20	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	160			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.5A; I <sub>B</sub> =50mA			1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =0.5A; V <sub>CE</sub> =5V			1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =160V; I <sub>E</sub> =0			1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	70		240	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		100		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =10V		25		pF

◆ h<sub>FE</sub> Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

